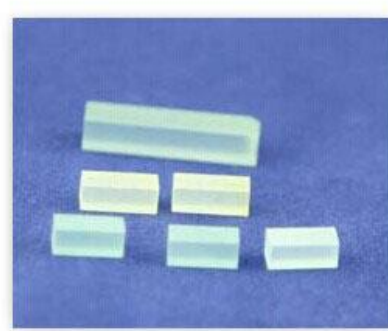


## Nd:YVO<sub>4</sub> Crystals

- Doping concentration range from 0.1% - 3%
- Various size bulk and finished crystals, size up to  $\varnothing 20 \times 20 \text{mm}$
- A variety of coatings are available

Neodymium doped Gadolinium Vanadate or Nd:YVO<sub>4</sub> crystal is one of the most efficient laser host crystal for DPSS lasers. Its large stimulated emission cross-section at lasing wavelength, high absorption coefficient and wide absorption bandwidth at pump wavelength, high damage threshold as well as good physical, optical and mechanical properties make Nd:YVO<sub>4</sub> an excellent crystal for high power, stable and cost effective DPSS lasers. Hangzhou Shalom EO offers the **Nd:YVO<sub>4</sub>** with Nd doping range of 0.1%-3% and with size up to Diam20x20mm.



- Doping concentration range from 0.1% to 3%.
- Doping concentration tolerance:  $\pm 0.05\%$  (atm% < 1%),  $\pm 0.1\%$  (atm%  $\geq 1\%$ ).
- Various size bulk and finished high quality **Nd:YVO<sub>4</sub> crystals** up to  $\Phi 20 \times 20 \text{mm}^3$ , respectively;
- Both ends AR/AR-1064/808nm, R < 0.2% @ 1064nm, R < 2% @ 808nm
- S1:HR@1064&532 nm, HT808 nm, R > 99.8% @ 1064&532nm, T > 90% @ 808nm  
S2:AR@1064&532 nm, R < 0.2% @ 1064nm, R < 0.5% @ 532nm
- S1:HR@1064, HT808, R > 99.8% @ 1064nm, T > 95% @ 808nm S2:AR@1064, R < 0.1% @ 1064nm.
- S1, S2 AR-coated, S3:gold/chrome plated.
- Both ends AR/AR-1064 nm; S3:AR-808 nm
- Other coatings are available upon request.

Specifications	
Transmitting wavefront distortion	less than $\lambda/4$ @ 633nm
Clear aperture	>90% central area
Chamfer	$\leq 0.2\text{mm}@45\text{degree}$
Chip	$\leq 0.1\text{mm}$
Flatness	$\lambda/8$ @ 633 nm
Scratch/Dig	10/5
Parallelism	better than 10arc seconds
Perpendicularity	$\leq 5$ arc minutes
Angle tolerance	$\leq 0.5^\circ$
Quality Warranty Period	one year under proper use

Physical and optical properties	
Atomic Density	$1.26 \times 10^{20}$ atoms/cm <sup>3</sup> (Nd1.0%)
Crystal Structure	Zircon Tetragonal, space group D <sub>4h</sub> -I <sub>4</sub> /amd a=b=7.1193Å, c=6.2892Å
Density	4.22g/cm <sup>3</sup>
Mohs Hardness	4-5(Glass-like)
Thermal Expansion Coefficient(300K)	$\alpha_a = 4.43 \times 10^{-6}/\text{K}$ $\alpha_c = 11.37 \times 10^{-6}/\text{K}$
Thermal Conductivity Coefficient(300K)	//C:0.0523W/cm/K ⊥C:0.0510W/cm/K
Lasing wavelength	1064nm, 1342nm
Thermal optical coefficient (300K)	$dn_o/dT = 8.5 \times 10^{-6}/\text{K}$ $dn_e/dT = 2.9 \times 10^{-6}/\text{K}$
Stimulated emission cross-section	$25 \times 10^{-19} \text{cm}^2 @ 1064\text{nm}$
Fluorescent lifetime	90μs(1% Nd doping)
Absorption coefficient	$31.4 \text{cm}^{-1} @ 810\text{nm}$
Intrinsic loss	$0.02 \text{cm}^{-1} @ 1064\text{nm}$
Gain bandwidth	0.96nm@1064nm
Polarized laser emission	n polarization; parallel to optic axis(c-axis)
Diode pumped optical to optical efficiency	>60%
Sellemeier equations ( $\lambda$ in μm)	$n_o^2 = 3.77834 + 0.069736/(\lambda^2 - 0.04724) - 0.010813\lambda^2$ $n_e^2 = 4.59905 + 0.110534/(\lambda^2 - 0.04813) - 0.012676\lambda^2$

### **Nd:YVO4's advantages over Nd:YAG**

As high as about five times larger absorption efficient over a wide pumping bandwidth around 808 nm (therefore, the dependency on pumping wavelength is much lower and a strong tendency to the single mode output).

As large as three times larger stimulated emission cross-section at the lasing wavelength of 1064nm. Lower lasing threshold and higher slope efficiency.

As a uniaxial crystal with a large birefringence, the emission is only linearly polarized.

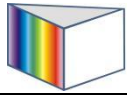
### **Laser Properties of Nd:YVO4**

1. One of the most attractive character of Nd:YVO4 is, compared with Nd:YAG, it has 5 times larger absorption coefficient in a broader absorption bandwidth around the 808 nm peak pump wavelength, which just matches the standard of high power laser diodes currently available. This means a smaller **Nd:YVO4 crystal** that could be used for the laser, leading to a more compact laser system. For a given output power, this also means a lower power level at which the laser diode operates, thus extending the lifetime of the expensive laser diode. The broader absorption bandwidth of Nd:YVO4 which may reaches 2.4 to 6.3 times that of Nd:YAG, is also valuable. Besides more efficient pumping, Nd:YVO4 also means a broader range of selection of diode specifications. This will be helpful to laser system makers for wider tolerance and lower cost choice.

2. Nd:YVO4 crystal has larger stimulated emission cross-sections, both at 1064nm and 1342nm. When a-axis cut Nd:YVO4 crystal lasing at 1064nm, it is about 4 times higher than that of Nd:YAG, while at 1340nm the stimulated cross-section is 18 times larger, which leads to a CW operation completely outperforming Nd:YAG at 1320nm. These make Nd:YVO4 laser be easy to maintain a strong single line emission at the two wavelengths.

3. Another important character of Nd:YVO4 lasers is, because it is an uniaxial rather than a high symmetry of cubic as Nd:YAG, what it emits is only a linearly polarized, thus avoiding undesired birefringent effects on the frequency conversion. Although the lifetime of Nd:YVO4 is about 2.7 times shorter than that of Nd:YAG, its slope efficiency can be still quite high for a proper design of laser cavity, because of its high pump quantum efficiency.

The major laser properties of Nd:YVO4 vs Nd:YAG are listed in Table below, including stimulated emission cross-sections ( $\sigma$ ), Absorption Coefficient ( $\alpha$ ) Fluorescent lifetime ( $\tau$ ), Absorption Length ( $L_a$ ), threshold Power ( $P_{th}$ ) and Pump Quantum Efficiency ( $\eta_p$ ).



**Laser Properties of Nd:YVO4 vs Nd:YAG**

LASER CRYSTAL	DOPING (atm%)	$\sigma$ ( $\times 10^{-19} \text{cm}^2$ )	$\alpha$ ( $\text{cm}^{-1}$ )	$\tau$ ( $\mu\text{s}$ )	La (mm)	Pth (mW)	$\eta_s$ (%)
Nd:YVO4(a-cut)	1.0	25	31.2	90	0.32	30	52
	2.0	25	72.4	50	0.14	78	48.6
Nd:YVO4(c-cut)	1.1	7	9.2	90		231	45.5
Nd:YAG	0.85	6	7.1	230	1.41	115	38.6

**Typical Results of Nd:YVO4:**

Diode pumped Nd:YVO4 laser output comparing with diode pumped Nd:YAG laser.

Crystals	Size (mm <sup>3</sup> )	Pump Power	Output (at 1064nm)
Nd:YVO4	3x3x1	850mW	350mW
Nd:YVO4	3x3x5	15W	6W
Nd:YAG	3x3x2	850mW	34mW

- Diode pumped Nd:YVO4+KTP green laser
- 8W green laser was generated from a 15W LD pumped 0.5% Nd:YVO4 with intracavity KTP
- 200mW green outputs are generated from 1W LD pumped 2% Nd:YVO4 lasers